

Device Modeling Report

COMPONENTS: Light-Emitting Diode (LED) STANDARD
PART NUMBER: SLP-WB89A-51
MANUFACTURER: SANYO
REMARK: TA=25 degree C

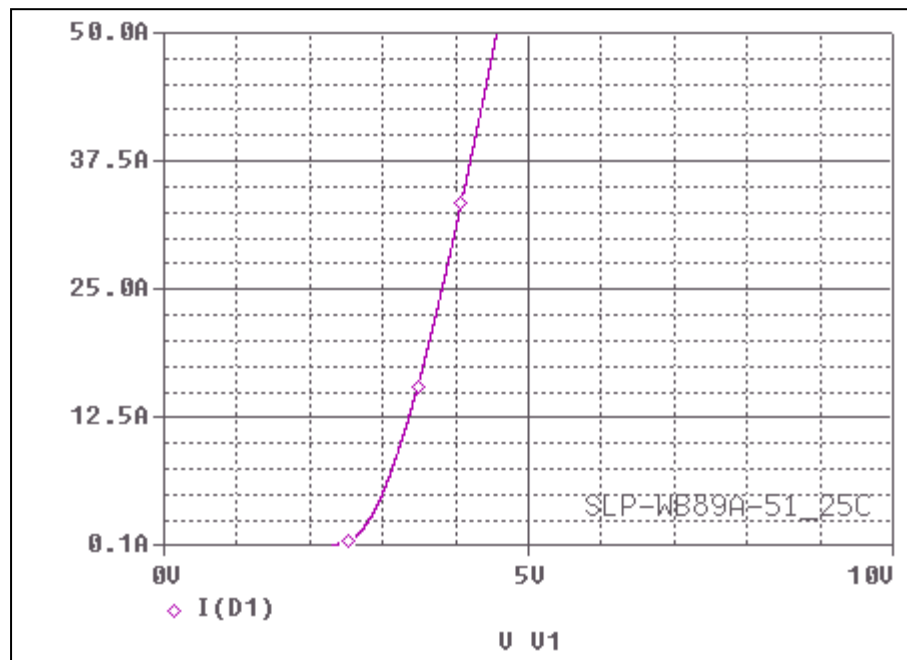


Bee Technologies Inc.

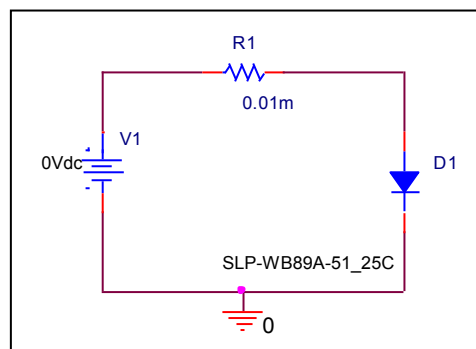
PSpice model parameter	Model description
IS	Saturation Current
N	Emission Coefficient
RS	Series Resistance
IKF	High-injection Knee Current
CJO	Zero-bias Junction Capacitance
M	Junction Grading Coefficient
VJ	Junction Potential
ISR	Recombination Current Saturation Value
BV	Reverse Breakdown Voltage(a positive value)
IBV	Reverse Breakdown Current(a positive value)
TT	Transit Time
EG	Energy-band Gap

Forward Current Characteristic

Circuit Simulation Result

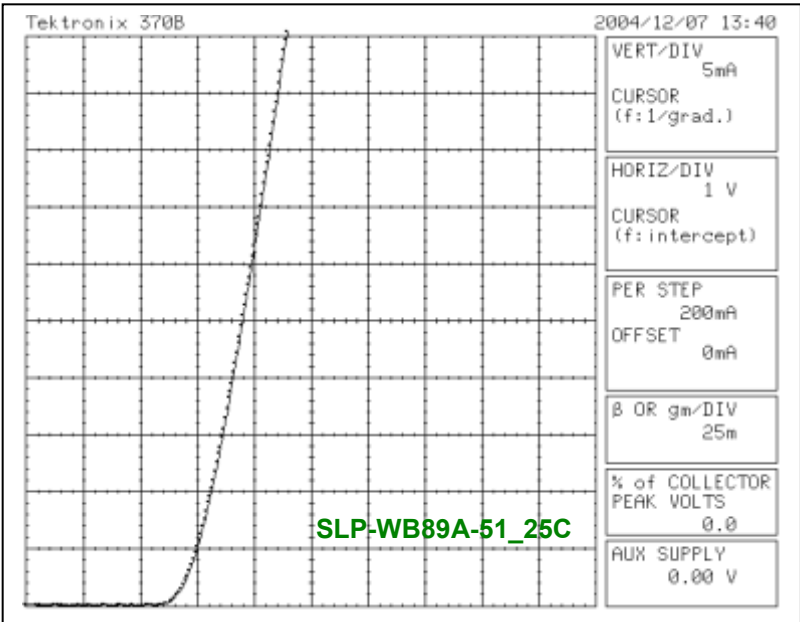


Evaluation Circuit



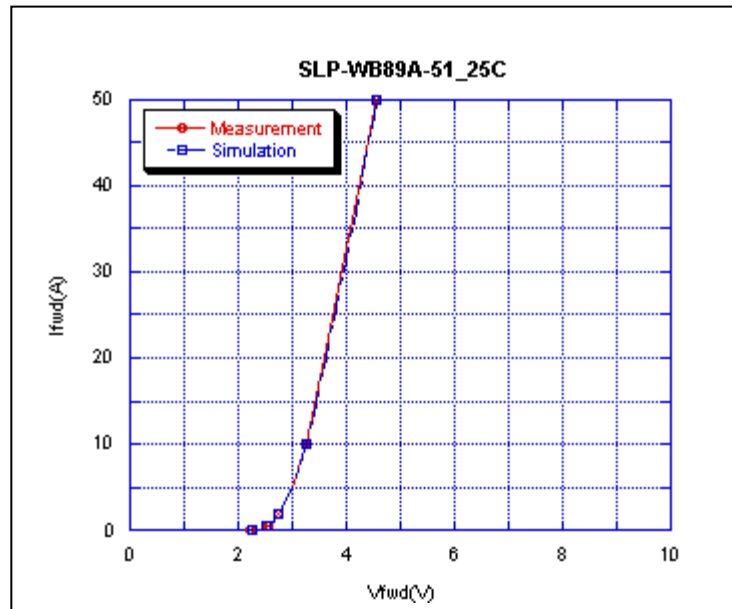
Forward Current Characteristic

Reference



Comparison Graph

Circuit Simulation Result

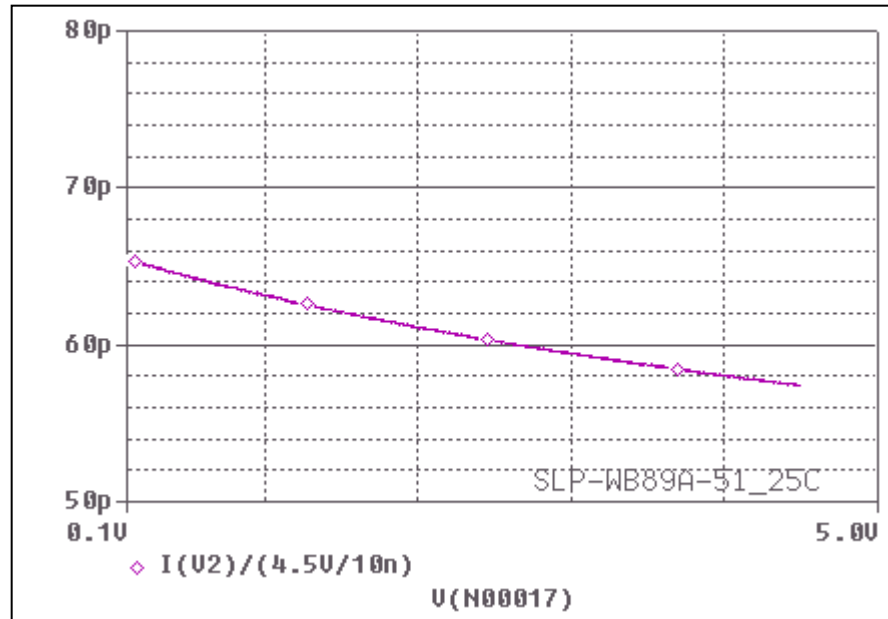


Simulation Result

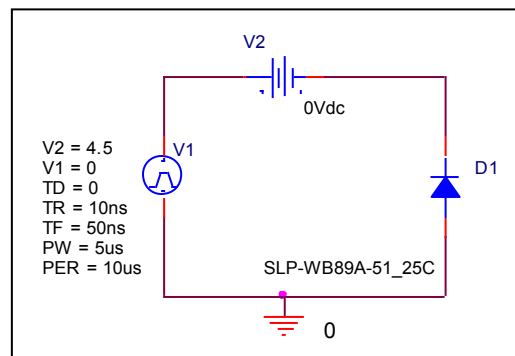
I_{fwd} (A)	V_{fwd} (V) Measurement	V_{fwd} (V) Simulation	%Error
0.1	2.21	2.25	1.80995
0.2	2.44	2.4	1.63934
0.5	2.57	2.52	1.94552
1	2.65	2.65	0
2	2.76	2.76	0
5	3.01	2.99	0.66445
10	3.26	3.248	0.36809
20	3.61	3.64	0.83102
50	4.57	4.56	0.21881

Capacitance Characteristic

Circuit Simulation Result

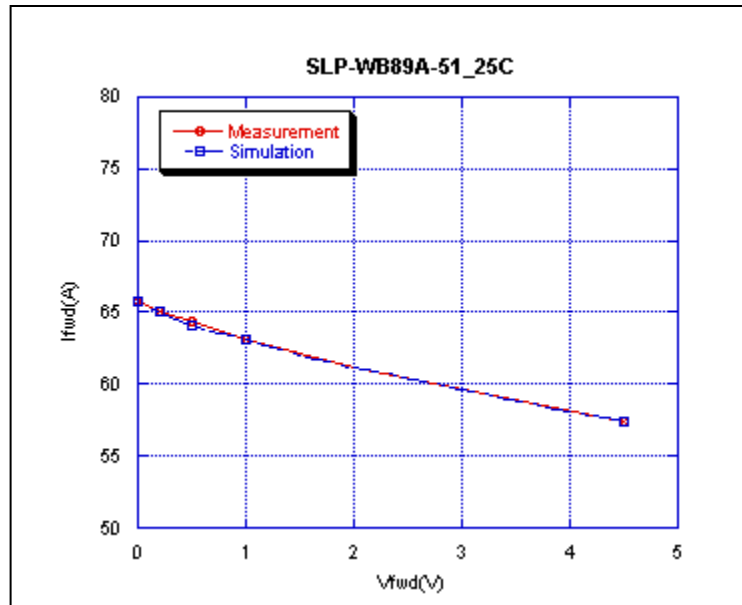


Evaluation Circuit



Comparison Graph

Circuit Simulation Result

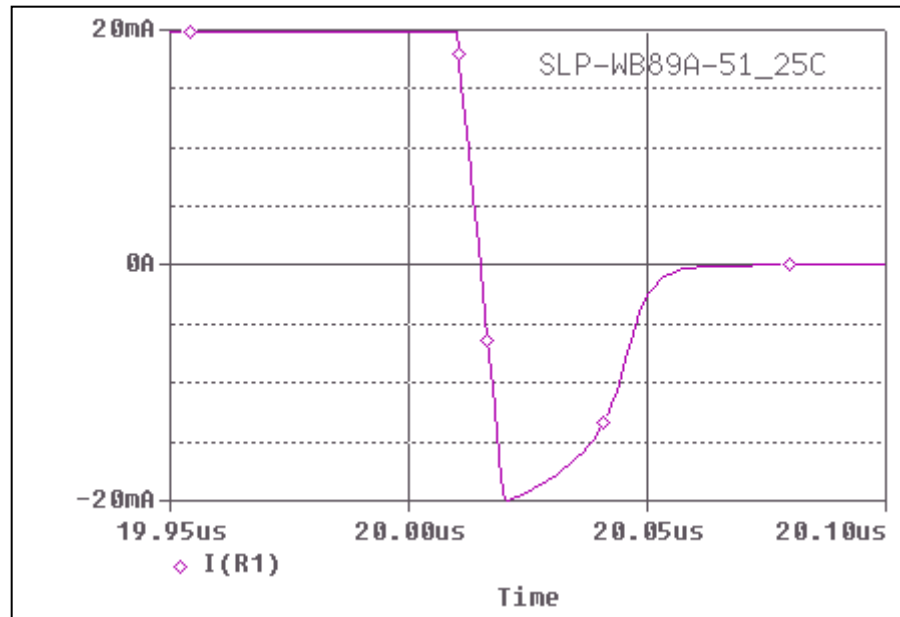


Simulation Result

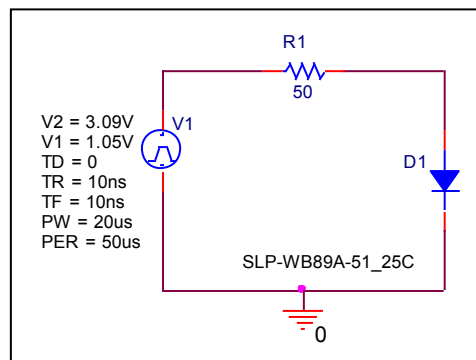
Vrev(V)	Cj(pF) Measurement	Cj(pF) Simulation	%Error
0	65.73	65.73	0
0.1	65.46	65.4	0.09165
0.2	65.12	65.11	0.01535
0.5	64.3	64.14	0.24883
1	63.12	63.14	0.03168
2	61.16	61.11	0.08175
4.5	57.39	57.39	0

Reverse Recovery Characteristic

Circuit Simulation Result



Evaluation Circuit

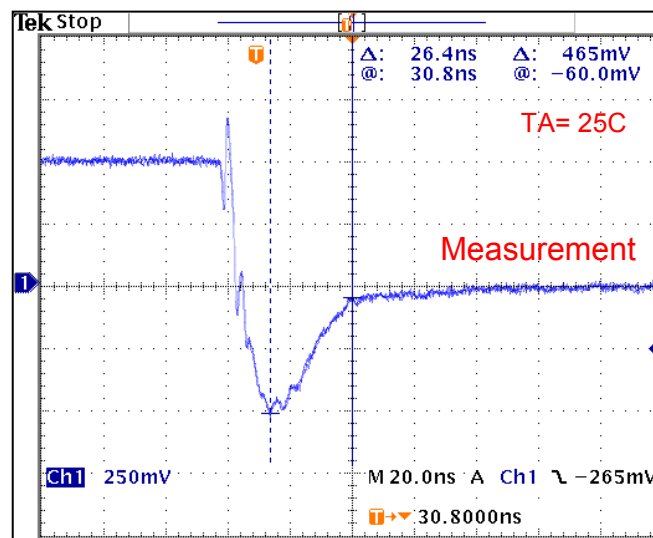


Compare Measurement vs. Simulation

Symbol	Measurement	Unit	Simulation	Unit	%Error
$T_{rr}=t_{rj}+t_{rb}$	34.8	ns	34.9	ns	0.2873

Reverse Recovery Characteristic

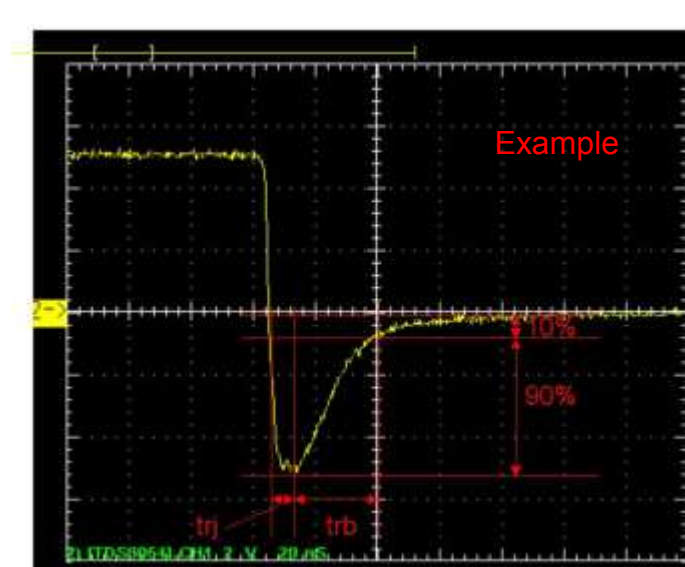
Reference



$T_{rj} = 8.4(\text{ns})$

$T_{rb} = 26.4(\text{ns})$

Conditions: $I_{fwd} = I_{rev} = 0.02(\text{A})$, $R_I = 50$



Relation between t_{rj} and t_{rb}